0.15

0.05



GENERAL PURPOSE AMPLIFIER

Typical Applications

- Broadband, Low Noise Gain Blocks
- IF or RF Buffer Amplifiers
- Driver Stage for Power Amplifiers
- Final PA for Low Power Applications
- Broadband Test Equipment

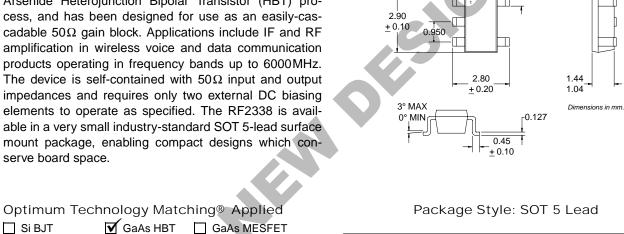
1.60

± 0.01

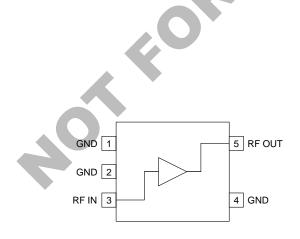
Product Description

☐ Si Bi-CMOS

The RF2338 is a general purpose, low-cost RF amplifier IC. The device is manufactured on an advanced Gallium Arsenide Heterojunction Bipolar Transistor (HBT) process, and has been designed for use as an easily-cascadable 50Ω gain block. Applications include IF and RF amplification in wireless voice and data communication products operating in frequency bands up to 6000MHz. The device is self-contained with 50Ω input and output impedances and requires only two external DC biasing elements to operate as specified. The RF2338 is available in a very small industry-standard SOT 5-lead surface mount package, enabling compact designs which conserve board space.



Features



SiGe HBT

Si CMOS

Functional Block Diagram

DC to 6000MHz Operation Internally Matched Input and Output 12dB Small Signal Gain • +24dBm Output IP3 +11dBm Output Power Single Positive Power Supply

Ordering Information RF2338 General Purpose Amplifier RF2338 PCBA Fully Assembled Evaluation Board Tel (336) 664 1233 RF Micro Devices, Inc. 7625 Thorndike Road Fax (336) 664 0454 Greensboro, NC 27409, USA http://www.rfmd.com

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RF2338

Absolute Maximum Ratings

| Parameter | Rating | Unit | | | |
|-------------------------------|-------------|------|--|--|--|
| Supply Current | 75 | mA | | | |
| Input RF Power | +15 | dBm | | | |
| Operating Ambient Temperature | -40 to +85 | °C | | | |
| Storage Temperature | -60 to +150 | °C | | | |



RF Micro Devices believes the furnished information is correct and accurate at the time of this printing. However, RF Micro Devices reserves the right to make changes to its products without notice. RF Micro Devices does not assume responsibility for the use of the described product(s).

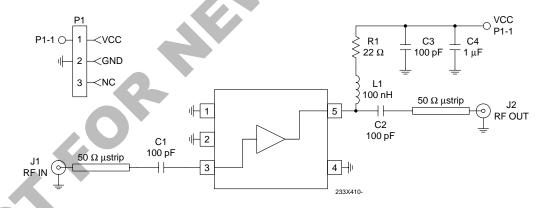
| Parameter | | Specification | | Unit | Condition | |
|--------------------------|------|---------------|------|------|---|--|
| Farameter | Min. | Тур. | Max. | Unit | Condition | |
| Overall | | | | | T=25°C, I _{CC} =40 mA | |
| Frequency Range | | DC to 6000 | | MHz | | |
| 3dB Bandwidth | | 3.5 | | GHz | | |
| Gain | | 12.1 | | dB | Freq=100MHz | |
| | | 11.8 | | dB | Freq=1000MHz | |
| | | 11.2 | | dB | Freq=2000MHz | |
| | | 9.7 | | dB ◀ | Freq=3000MHz | |
| | | 8.7 | | dB | Freq=4000MHz | |
| | | 8 | | dB | Freq=5000MHz | |
| | | 7.3 | | dB | Freq=6000MHz | |
| Gain Flatness | | ±0.5 | | dB | 100MHz to 2000MHz | |
| Noise Figure | | 5.3 | | dB | Freq=2000MHz | |
| Input VSWR | | 2.0:1 | | | In a 50Ω system, DC to 3000MHz | |
| Output VSWR | | 2.0:1 | | | In a 50Ω system, DC to 3000MHz | |
| Output IP ₃ | | +24 | | dBm | Freq=2000MHz±50kHz, P _{TONE} =-10dBm | |
| Output P _{1dB} | | +10.5 | | dBm | Freq=2000MHz | |
| Reverse Isolation | | 15.6 | | dB | Freq=2000MHz | |
| Power Supply | | | | | With 22Ω bias resistor | |
| Device Operating Voltage | | 3.6 | | V | At pin 5 with I _{CC} =40mA | |
| Operating Current | | 40 | | mA | | |

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| Pin | Function | Description | Interface Schematic |
|-----|----------|--|---------------------|
| 1 | GND | Ground connection. Keep traces physically short and connect immediately to ground plane for best performance. | |
| 2 | GND | Same as pin 1. | |
| 3 | RF IN | RF input pin. This pin is NOT internally DC blocked. A DC blocking capacitor, suitable for the frequency of operation, should be used in most applications. DC coupling of the input is not allowed, because this will override the internal feedback loop and cause temperature instability. | |
| 4 | GND | Same as pin 1. | |
| 5 | RF OUT | RF output and bias pin. Biasing is accomplished with an external series resistor and choke inductor to V_{CC} . The resistor is selected to set the DC current into this pin to a desired level. The resistor value is determined by the following equation: $R = \frac{(V_{SUPPLY} - V_{DEVICE})}{I_{CC}}$ Care should also be taken in the resistor selection to ensure that the current into the part never exceeds 75mA over the planned operating temperature . This means that a resistor between the supply and this pin is always required, even if a supply near 3.6V is available, to provide DC feedback to prevent thermal runaway. Because DC is present on this pin, a DC blocking capacitor, suitable for the frequency of operation, should be used in most applications. The supply side of the bias network should also be well bypassed. | RF IN O |

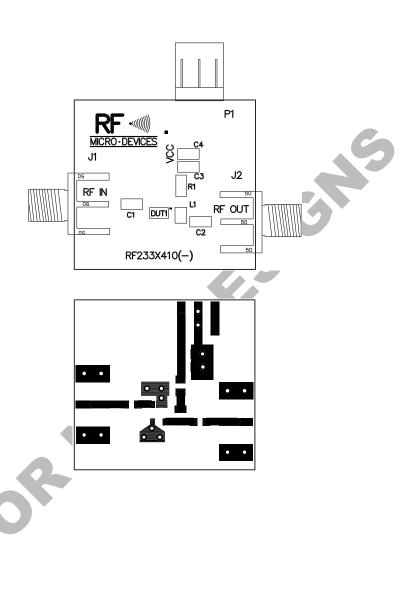
Evaluation Board Schematic

(Download Bill of Materials from www.rfmd.com.)



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Evaluation Board Layout Board Size 1" x 1"



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